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OPTO TECHNOLOGY INC

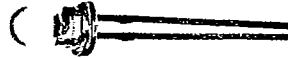
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T-41-51

OPTO TECHNOLOGY

PN SILICON PHOTODIODE

TYPE OT 423

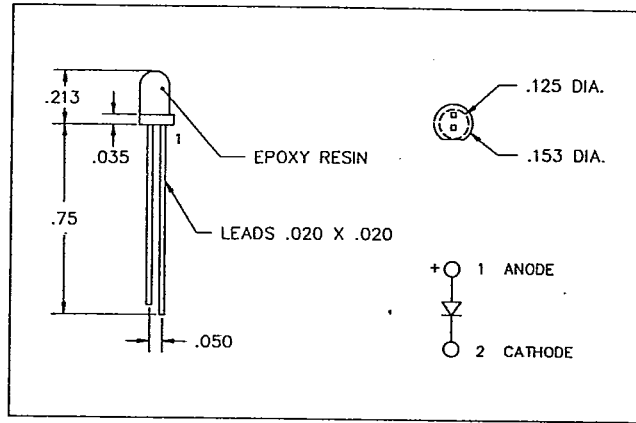


Features

- Low cost
- High speed
- T-1 plastic package

Description

Opto Technology's OT 423 consists of a PN junction silicon photodiode mounted in a clear plastic, end-looking T-1 package. The device offers high speed and sensitivity and has an acceptance half angle of 16 degrees measured from the optical axis to the half power point.



Absolute Maximum Ratings⁽⁴⁾

Reverse Voltage	20 V
Storage Temperature Range	-20°C to +80°C
Operating Temperature Range	-20°C to +80°C ⁽³⁾
Lead Soldering Temperature (1/16 inch [1.6 mm] from case for 5 sec. with soldering iron)	240°C ⁽¹⁾
Power Dissipation	100 mW ⁽²⁾

Notes:

- (1) RMA flux is recommended. Duration can be extended to 10 sec. max. when wave soldering.
- (2) Derate 1.80 mW/°C above 25°C ambient.
- (3) Light sources is unfiltered tungsten bulb operating at CT = 2870°K or equivalent infrared source.
- (4) T_A = 25°C unless otherwise noted.

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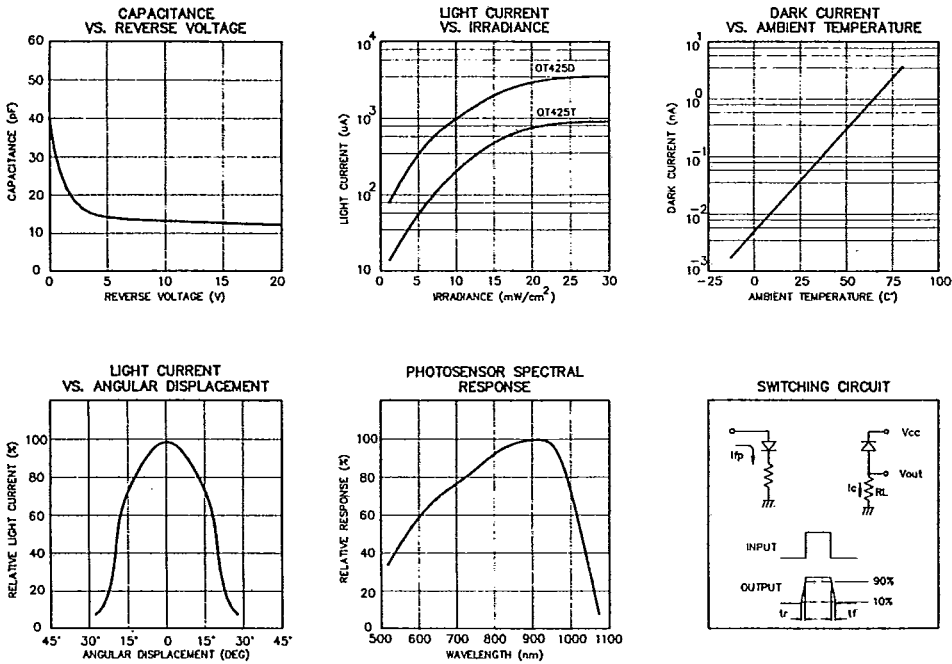
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Electrical Characteristics: (25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS
Open Circuit Voltage $H = 1 \text{ mW/cm}^2$ (3)	V_{OC}		.4		V
Light Current $H = 1 \text{ mW/cm}^2$ (3)	I_L	6	12		μA
Dark Current $V_R = 5\text{V}$	I_D			500	nA
Reverse Breakdown Voltage $I_R = 100\mu\text{A}$	$V_{(BR)R}$	20			V
Total Capacitance, $V = 0, f = 1\text{MHZ}$	C_t		4		pF
Spectral Sensitivity	λ	450		1050	nm
Peak Wavelength	λ_P		900		nm
Rise Time $V_R = \text{ , } R_L = 1\text{K}\Omega$	t_r		1		μs
Fall Time $V_R = \text{ , } R_L = 1\text{K}\Omega$	t_f		1		μs
Half Angle	ϕ_H		± 16		deg

SILICON PHOTODIODES

TYPICAL PERFORMANCE CURVES



Opto Technology reserves the right to make changes at any time to improve product design and reliability.